

Silicon NPN Power Transistors

2SD1136

DESCRIPTION

www.datasheet4u.com

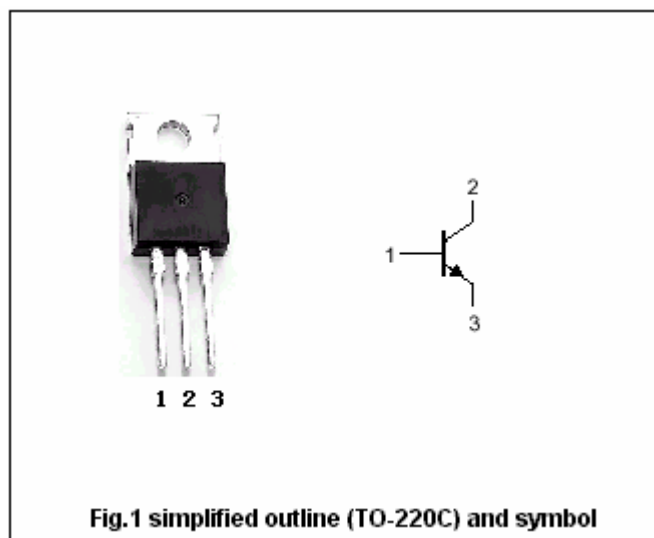
- With TO-220C package
- High collector-base breakdown voltage
: $V_{CBO}=200V(\text{min})$

APPLICATIONS

- For power switching and TV vertical deflection output applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

Absolute maximum ratings($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	200	V
V_{CEO}	Collector-emitter voltage	Open base	80	V
V_{EBO}	Emitter-base voltage	Open collector	5	V
I_C	Collector current		4	A
I_{CM}	Collector current-Peak		5	A
P_C	Collector power dissipation	$T_a=25^\circ\text{C}$	1.8	W
		$T_C=25^\circ\text{C}$	30	
T_j	Junction temperature		150	$^\circ\text{C}$
T_{stg}	Storage temperature		-45~150	$^\circ\text{C}$

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CHARACTERISTICS

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 $T_j=25^\circ\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	$I_C=50\text{mA}; I_B=0$	80			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	$I_E=1\text{mA}; I_C=0$	5			V
V_{CEsat}	Collector-emitter saturation voltage	$I_C=4\text{A}; I_B=0.4\text{A}$			1.5	V
V_{BEsat}	Base-emitter saturation voltage	$I_C=4\text{A}; I_B=0.4\text{A}$			1.5	V
I_{CEO}	Collector cut-off current	$V_{CE}=200\text{V}; I_B=0$			50	μA
I_{EBO}	Collector cut-off current	$V_{EB}=5\text{V}; I_C=0$			50	μA
h_{FE}	DC current gain	$I_C=4\text{A}; V_{CE}=5\text{V}$	20			

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PACKAGE OUTLINE

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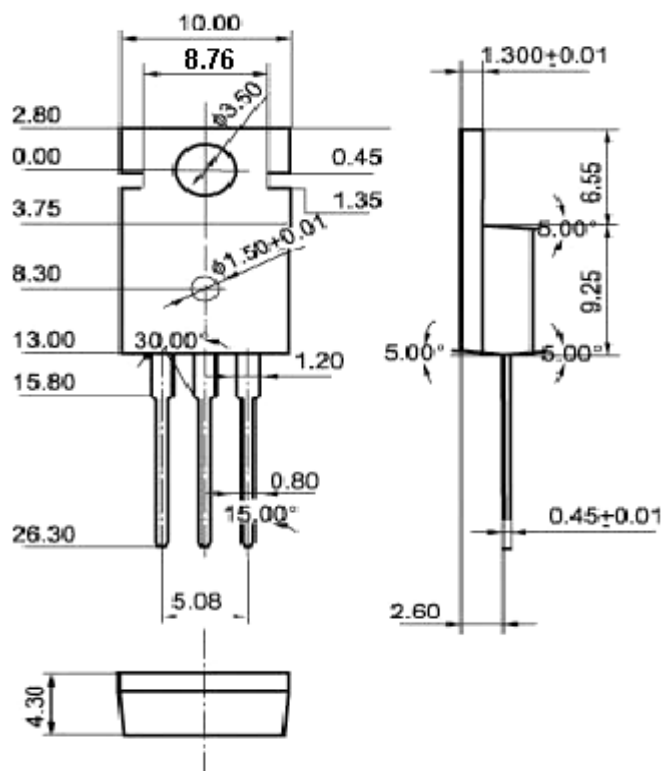


Fig.2 Outline dimensions (unindicated tolerance:±0.10 mm)